## NSN 5961-01-277-3281

Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:
Glass
Overall Length:
Between 0.293 inches and 0.357 inches
Terminal Length:
Between 1.000 inches and 1.625 inches
Overall Diameter:
Between 0.215 inches and 0.235 inches
Function For Which Designed:
Transient suppressor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
Do-13
Mounting Method:
Terminal
Features Provided:
Quality assurance level txv
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
105.0 breakdown voltage, dc and 116.0 breakdown voltage, dc and 94.0 working peak reverse voltage
Current Rating Per Characteristic:
5.00 microamperes forward current, average peak
Power Rating Per Characteristic:
1.0 watts small-signal input power, common-collector major
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius ambient air
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/500 government specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0